

Universität Augsburg Mathematisch-Naturwissenschaftliche Fakultät

Investigation and Manipulation of Dislocations in Heteroepitaxial Diamond-on-Iridium Crystals

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Session II: Diamond Characterization



Outline

- Diamond for Radiation and Particle Detectors
- Growth of Heteroepitaxial Diamond Films on Ir/YSZ/Si(001)
- Defects in Crystals
- Dislocations in CVD Diamond
- Detection of Dislocations
- Reduction of Dislocation Density
- Further investigations

Influence of material quality on detector performance

Local variation of sensitivity

→ Electronic activity of crystal lattice defects and impurities (recombination centres)

X-ray response of a homoepitaxial single crystal diamond detector



J. Morse, CARAT Workshop 2009

X-ray response of a polycrystalline diamond detector



Fig. 3. Image of the X-ray sensitivity as measured on a 1=1 mm area in the corner of the electrical contact. Grey scale is logarithmic and given in nA, for a 2.2= 10^8 ph s^{y 1} flux at 5.5 keV.

P. Bergonzo et al., DRM 11 (2002), 418

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Method of growth

Microwave enhanced plasma chemical vapour deposition (MWPCVD)



Schematic and photograph of CVD reactor



Substrate

Multi-layer system Ir/YSZ/Si(001) (YSZ = yttria-stabilised zirconia)

- → Good thermal compatibility of diamond and silicon
- \rightarrow Monocrystalline growth of diamond on iridium
- \rightarrow Cost-saving (Ir price!) due to thin film technology



Thermally induced stress due to mismatched thermal expansion coefficients of diamond and substrate



Schematic of diamond/Ir/YSZ/Si multi-layer system

Nucleation

Bias-Enhanced Nucleation (BEN)

- \rightarrow Applicable to 4 inch Ir/YSZ/Si(001) wafers
- → Nucleation density up to 10^{11} cm⁻²



Schematic of BEN set-up



4 inch substrates for BEN process

Heteroepitaxial Diamond Films on Ir/YSZ/Si(001)

Growth

- \rightarrow Formation of defect-rich monocrystalline diamond film
- → Improvement of crystalline quality with film thickness



Schematic: Transition to heteroepitaxial diamond single crystal

SEM images of Dia/Ir/SrTiO₃/Si(001)

Heteroepitaxial Diamond Films on Ir/YSZ/Si(001)

State of the art 10 x 10 mm² flawless detector Large-area growth crystal \rightarrow Step by step towards 30 x 30 mm² HadronPhysics2 20 x 20 mm² neutron monochromator crystals Study of Strongly ("poor" quality) 2274 18 x 18 mm² attempt for detector crystal (medium quality, still many inclusions) 0

MP

11

• State of the art

Detector performance

 \rightarrow Resolution of discrete mixed nuclide α particle energy spectrum



wik

Point defects (0-dimensional) e.g. vacancies and interstitials



C. Kittel: Einführung in die Festkörperphysik, 14th ed. (2006)



Planar defects (2-dimensional) e.g. grain boundaries Line defects (1-dimensional) e.g. dislocations



Bulk defects (3-dimensional) e.g. voids (= clusters of vacancies)

http://www.spaceflight.esa.int/impress/text/education/Glossary/Glossary_G.html

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• Basics



http://en.wikipedia.org/wiki/Dislocation

• Basics

Classification by Burgers vector **b** and dislocation line direction **I**

Determination of Burgers vector **b** of an edge dislocation



http://de.wikipedia.org/wiki/Versetzung_(Materialwissenschaft)

Dislocation line I (blue) of an edge dislocation



http://en.wikipedia.org/wiki/Dislocation

Edge dislocation:	$\mathbf{b} \perp \mathbf{I}$
Screw dislocation:	b I
Mixed dislocation:	else

Simplest types of dislocations in diamond

Perfect dislocations of the $\{111\}\langle 110\rangle$ slip system

- → Screw dislocation, e.g. $I_s = [1 1 0], b_s = 1/2 [1 1 0]$

- → 60° dislocation, e.g. $I_{60} = [1 1 0], b_{60} = 1/2 [0 1 1]$
 - Edge dislocation, e.g. $I_{e} = [-1 1 2], b_{e} = 1/2 [-1 1 0]$



This is only the tip of the iceberg!

A. Blumenau et al., Defects and Diffusion Forum 226-228 (2004) 11

Threading dislocations

Consequence of growth mechanism of heteroepitaxial diamond films

 \rightarrow Generation of defect bands composed of small angle grain boundaries



Film thickness 0.6 $\mu m,$ grain size 0.3 μm



Film thickness 8 μm, grain size 1 μm



Film thickness 34 µm, no well-defined grains



Film thickness 34 μ m, defect bands highlighted

Plan view TEM images of thin heteroepitaxial CVD diamond films

- → Dislocation lines penetrating the whole diamond film nearly parallel to the growth direction
- → Initially very high dislocation density, comparable to nucleation density (10¹¹ cm⁻²), decreasing with film thickness



C. Kittel: Einführung in die Festkörperphysik, 14th ed. (2006)

Common methods



Values taken from K. Sangwal: Etching of Crystals (1987)

Detection of Dislocations

Etching

Plasma etching of diamond

- \rightarrow Similar to CVD growth process
- → Addition of CO_2 instead of CH_4 in the gas phase
- → Formation of etch-pits at intersection of surface and dislocation line





SEM image of etch-pits in diamond

J. Achard et al., PSS(A) 206 (2009) 1949

Advantages:

- → Compatible with existing CVD reactors
- → Fast
- → Suitable for wide range of dislocation densities

Experimental observations on Dol films

Etch pit distribution on "low-quality" crystals for neutron monochromators



Dark-field optical microscope image

• Experimental observations on Dol films

Etch pit distribution on "low-quality" crystals for neutron monochromators



SEM image

Experimental observations on Dol films

Etch pit distribution on "low-quality" crystals for neutron monochromators



Bi-modal etch-pit distribution:

- \rightarrow Agglomerated dislocation bands from former grain boundaries
- \rightarrow Dispersed dislocations inside former grains

Extracted etch-pit positions

500

• Experimental observations on Dol films

Photoluminescence pattern on "high-quality" crystal for detectors

→ Blue luminescence correlated with dislocations



DiamondView image (UV excitation), courtesy of J. Achard

Experimental observations on Dol films

Photoluminescence pattern on "high-quality" crystal for detectors

→ Blue luminescence correlated with dislocations



Luminescence bands automatically extracted by Watershed Algorithm

 $\rightarrow~$ characteristic length scale ~ 35 μm



Experimental observations on Dol films

Unexpected similarity between "low-quality" monochromator crystals and "high-quality" detector crystals!



Further investigation necessary

- → Cathodoluminescence imaging (information depth!)
- \rightarrow Thickness dependent etch-pit distribution



• Growth of thick layers

A. Romanov et al., PSS(B) 198 (1996) 599



→ Common **1/d dependence** observed for other material systems

Growth of thick layers

Descriptive explanation: Interaction of inclined dislocations during growth

 \rightarrow Annihilation of dislocations with opposite Burgers vectors



→ Reduction of dislocation density by growth of thick layers possible



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• Experimental observations on Dol films

Etch pit density on films of different thickness



Experimental observations on Dol films

Etch pit density on films of different thickness







R.S. Balmer et al.: *Chemical vapour deposition synthetic diamond: material, technology and applications* J. Phys.: Condens. Matter 21 (2009) 364221

- TEM measurements
 - → Dislocation type
 - \rightarrow Dislocation line direction
- Creating larger etch-pit data set
 - \rightarrow Spatial etch-pit distribution at different growth stages
 - \rightarrow Dislocation density reduction and modelling of thickness dependence
- Correlation of etch-pits and Raman/luminescence measurements
- Investigation of etch-pit morphology
- Correlation with detector performance



Etch-pits of different size and shape

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